**SPR220-7.0 Profiles using Contact Aligner**

2) SPR220-7.0 (Positive Tone)

**Process:**
- Clean a Si wafer piece: Acetone (2’) + Methanol (1’) in ultrasonic cleaner; DI water resin and N₂ blow dry.
- Dehydration bake @ 110 °C for 5 minutes.
- Spin-on HMDS @ 3500 rpm for 30 seconds.
- Spin-on SPR220-7.0 resist @ 3500 rpm for 45 seconds.
- Soft bake @ 115 °C for 120 seconds.
- Resist edge bead removal: exposure time=120 seconds, development time=90 seconds in MF-701 developer.
- Expose resist for 60 seconds without a filter (7.5 mW/cm² using 405-nm detector).
- Wait for 5 minutes to let the resist finish the reaction.
- Develop the exposed resist pattern for 70 seconds in MF-701 developer.

**Result:**
**Figure 3 (a)** Resist profile; **(b)** Resist side-wall.

![Resist profile](image1)

**Note:** Resist Thickness=7.56 µm.